

Silicon Pixels and Strips

RD_FCC Referees Meeting
September 16th, 2020
Remote Connection

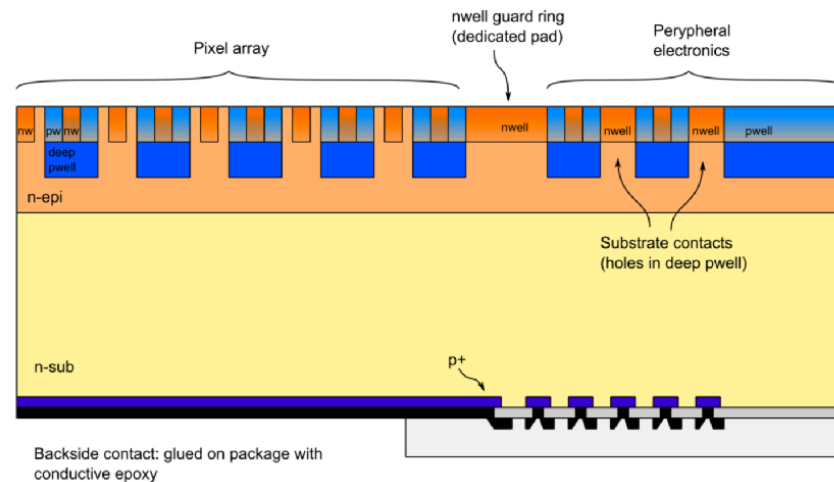


Istituto Nazionale di Fisica Nucleare

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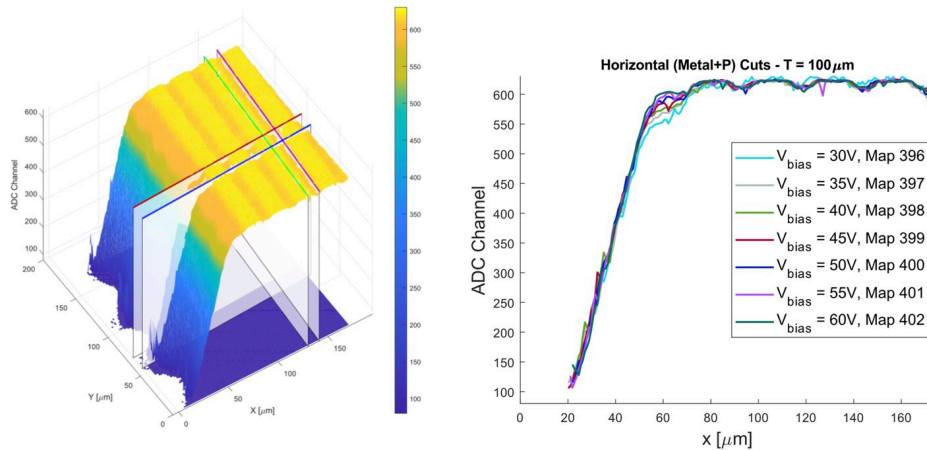
Ongoing activity towards a CMOS sensor design and fabrication platform allowing for:

- * Active sensor thickness in the range 50 μm to 500 μm or more;
- * Operation in full depletion with fast charge collection only by drift, small charge collecting electrode for optimal signal-to-noise ratio;
- * Scalable readout architecture with ultra-low power capability ($O(10 \text{ mW}/\text{cm}^2)$);
- * Compatibility with standard CMOS fabrication processes: concept study with small-scale test structure (SEED), technology demonstration with large area sensors (ARCADIA)
- * Technology: 110nm CMOS node (quad-well, both PMOS and NMOS), high-resistivity bulk
- * Custom patterned backside, patented process developed in collaboration with LFoundry

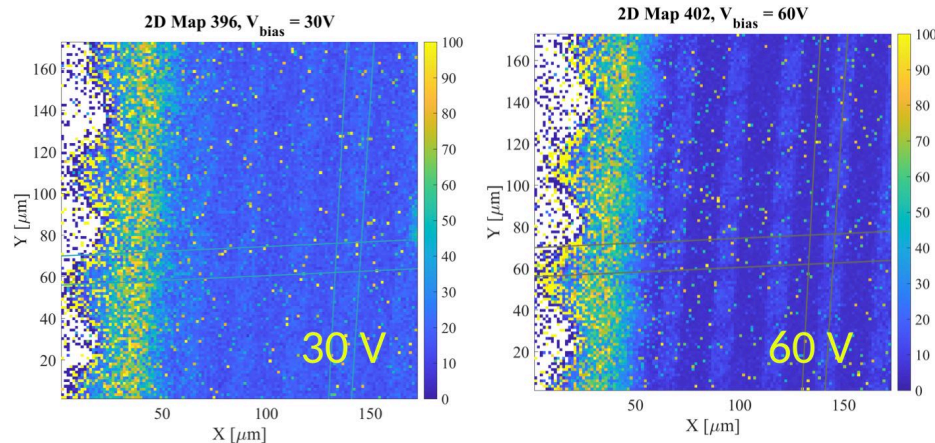


Characterisation with SEED pseudo-matrices

Cuts along the **Metal + P** and **Metal + N** lines on the energy map with varying bias voltages show **uniform CCE** above FD with **~1.7 % loss over metals** (100 μm thick)

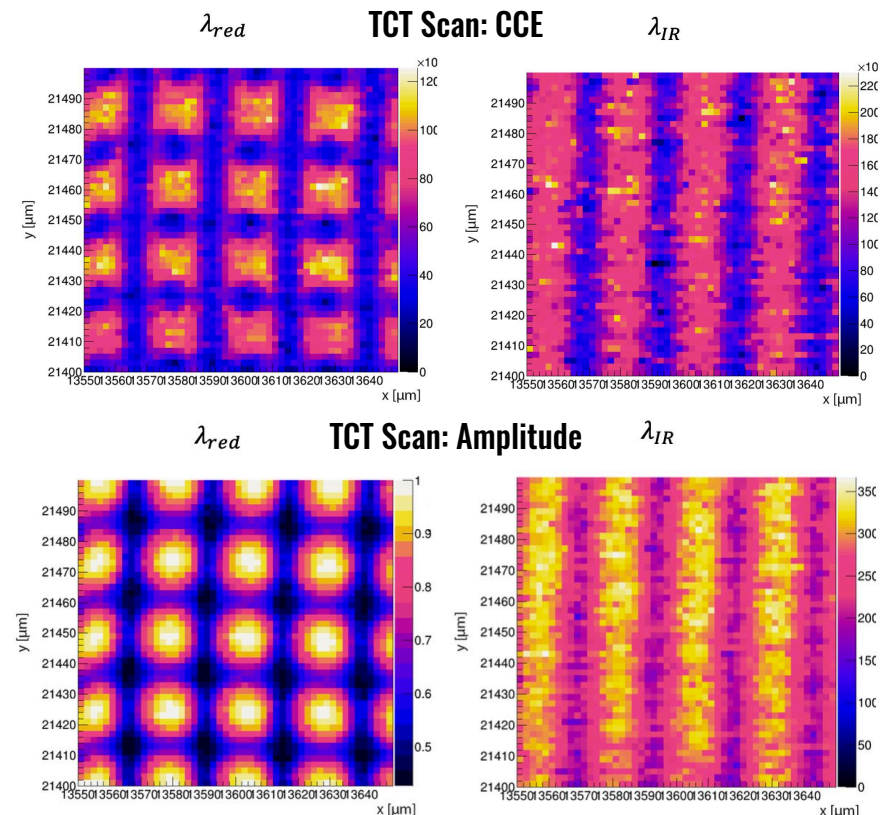


Standard deviation maps show the expected higher electronic noise when the sensor is not depleted (below 30 V), due to the higher top capacitance.



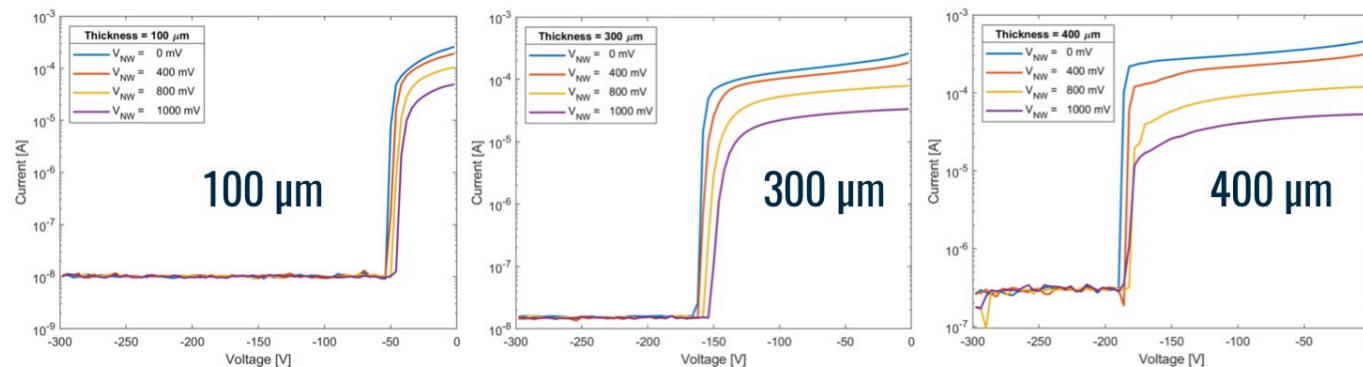
(**RUĐER BOŠKOVIĆ INSTITUTE**)* Zagreb, Croatia

- 600 keV to 2 MeV Tandetron
- TANDEM 1-6 MeV proton source
- LASER TCT laboratory

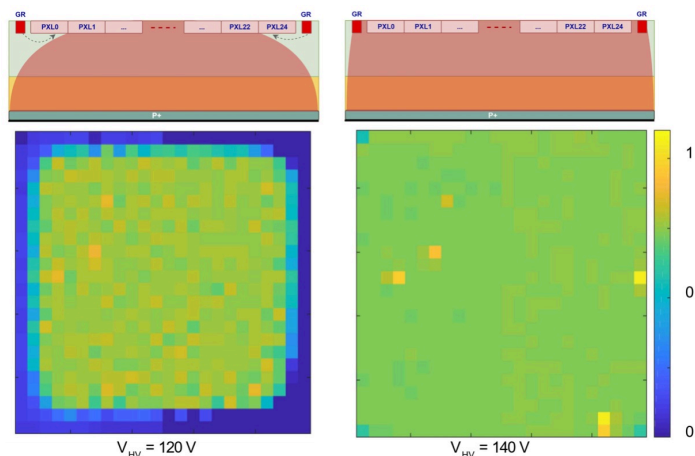


Characterisation with SEED MATISSE

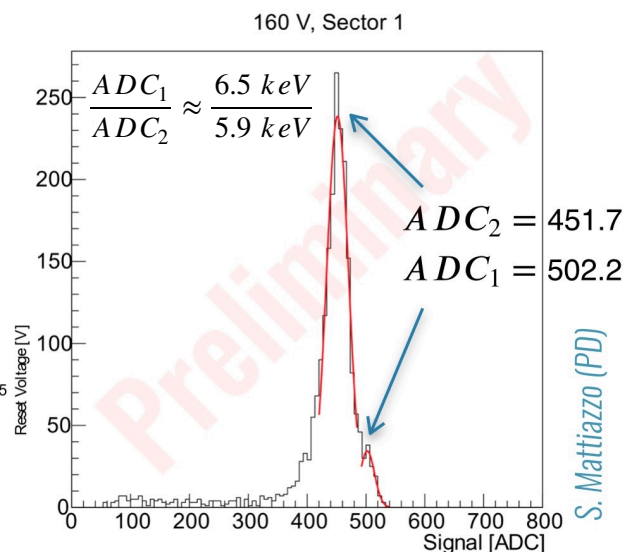
Full depletion studies in 100-300-400 μm prototypes



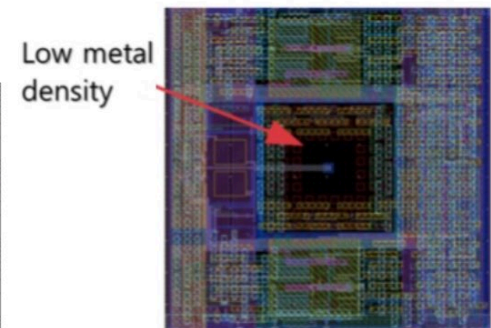
Map of pixel reset voltage (MATISSE 24x24 pixel matrix) as a function of the back-side voltage applied to the sensor. Depletion starts from the back-side.



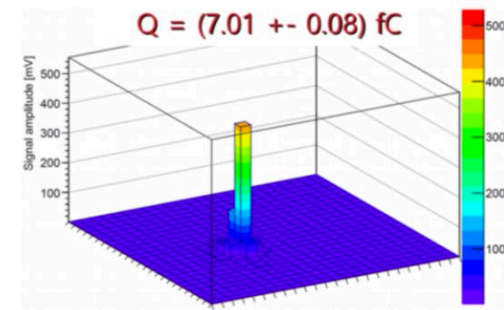
Preliminary results with ^{55}Fe



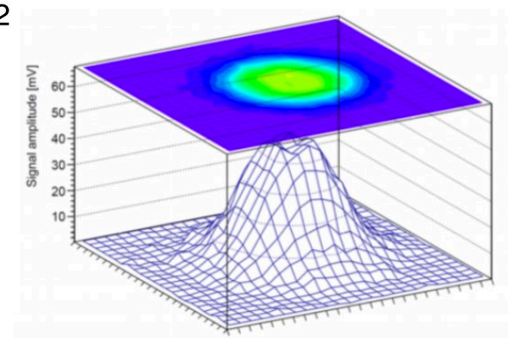
The ^{55}Fe emits monochromatic X-rays at 5.9 keV (K_α). A K_β line at 6.5 keV is also emitted with a relative probability below 5%.



Focused pulse

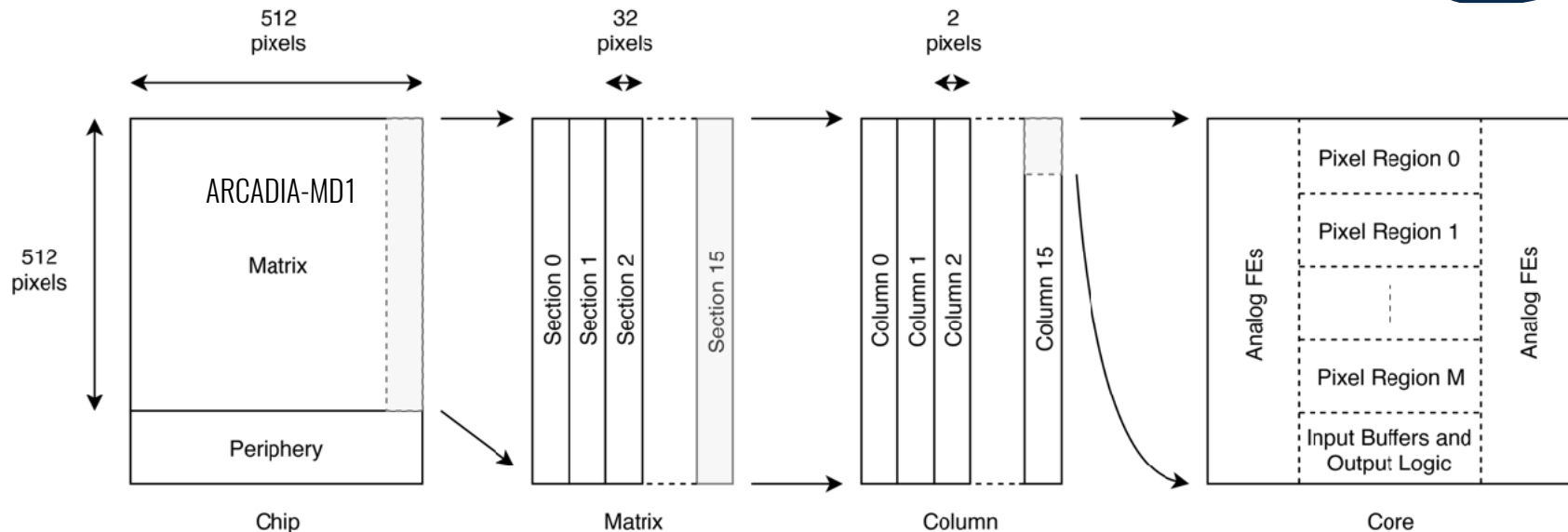


Non focused pulse



J. Olave FEE2018

ARCADIA - Demonstrator Chip



- * **Pixel size $25\ \mu\text{m} \times 25\ \mu\text{m}$** : process, back-side pattern and geometry validated in silicon (both MATISSE and pseudo-matrices, electrical, laser, radioactive source and microbeam).
- * Matrix core 512×512 , “side-abutable” to accommodate a **1024×512 silicon active area** ($2.56 \times 1.28\ \text{cm}^2$). Matrix and EoC architecture, data links and payload ID: scalable to **$2048 \times 2048^*$**
- * Triggerless binary data readout, event rate up to $10\text{-}100\ \text{MHz}/\text{cm}^2$
- * First engineering run with ARCADIA-MD1 by 09/2020, second full CMOS maskset during spring 2021, **funding available for 3 engineering runs** (secured over **0.4M€** extra funding from synergy with EU Projects)

Rimosso materiale “Internal Use Only”, contattare darochar@to.infn.it

ATLASpix3 Large Silicon Systems



* R&D for the large are part of the detector:

- ◆ All Si-tracker or Si-Wrapper for IDEA and TPC based tracking systems: 50-100 m²

* Proposal submitted to CEPC including interests from Italian groups:

- ◆ **China:** Harbin, IHEP, NWPU, Shandong, SJTU, Tsingua, UTSTC; **Germany:** KIT; **Italy:** Milano, Pisa, Torino; **UK:** Bristol, Daresbury, Edinburgh, Lancaster, Liverpool, RAL, Sheffield, Warwick

* Develop a full CMOS pixel solution:

- ◆ Full CMOS technology costs and power consumptions are becoming nearer to the strips
- ◆ If trend continues, it may effectively replace them with a more performant detector

CMS Upgrade	Double Strips	Macropixels+Strips	Hybrid Pixels	DMAPS@FCCee
Area	192 m ²	25 m ²	4.9 m ²	100-200 m ²
Power density	27 mW/cm ²	89 mW/cm ²	700 mW/cm ²	<150 mW/cm ²
Module cost (TDR)	26990 kCHF	20780 kCHF	11691 kCHF	
	140 kCHF/m ²	830 kCHF/m ²	2400 kCHF/m ²	400-500 kCHF/m ²

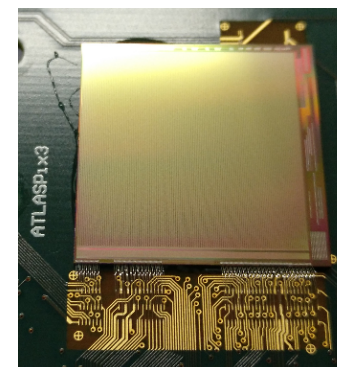
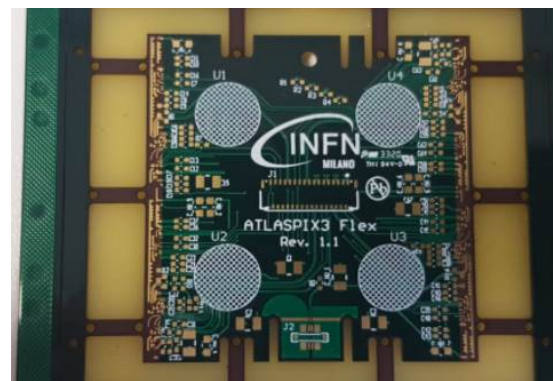
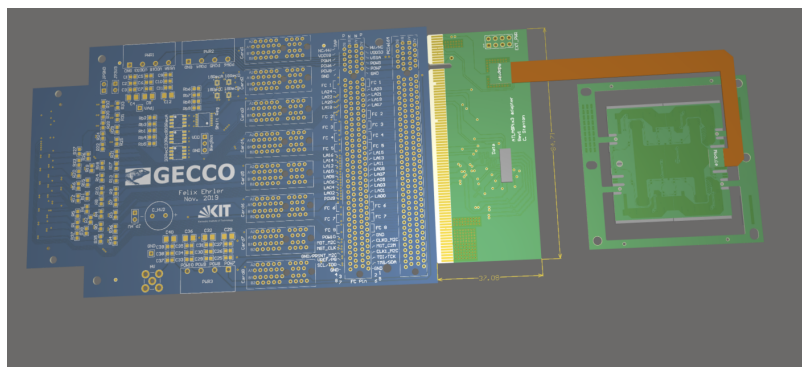
ATLASpix3 R&D plans

* Initial prototyping using ATLASPIX3

- ◆ Full size 2x2 cm chip from ATLAS developments
- ◆ Demonstrating module and mini-stave assembly
- ◆ Two wafers (one thinned to 150 μm) dedicated to the initial effort:
 - practicing the DAQ system (design by KIT, production done by Chinese groups, now begin distributed)
 - test module assembly (Milano): flex circuits now being populated
 - integration of modules in the test system (UK)

* Further generations of the sensors are in development:

- ◆ FCEPCPix1 in AMS,
- ◆ possible porting to other foundries



ATLASpix3 Financial requests for 2021



* **Perform a further iteration in module assembly:**

- ◆ current flex hybrid implementation followed the KISS (keep it simple and safe) principle;
- ◆ a second generation would implement features for use in system tests and a more realistic environment:
 - reduce number of layers (possible by dropping options implemented in the 2020 version)
 - design for operation within a serial powering chain

* **Additional sensors will be needed for building mini-staves**

- ◆ same masks as ATLASPIX3, so non-recurring costs already paid in ATLASPIX3 original submission.
Contributions from various FA, cost should be 2k€/wafer + taxes.

* **Funding requests:**

Categoria	Sez.	Capitolo		[k€]
3	MI	Consumi	Flex hybrid	5
3	MI	Consumi	Acquisto wafer ATLASPIX3 (2 wafer x 2.5 k€)	5